
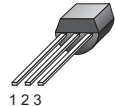


### HAOPIN MICROELECTRONICS CO.,LTD.

#### Description

Glass passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

<p>Symbol</p> 		<p>Simplified outline</p>  <p>TO-92</p>	
Pin	Description		
1	Cathode		
2	anode		
3	gate		
TAB	anode		

#### Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

#### Features

- ◆ Blocking voltage to 600 V
- ◆ On-state RMS current to 1.5 A
- ◆ Ultra low gate trigger current

SYMBOL	PARAMETER		Value	Unit
$V_{DRM}$	Repetitive peak off-state voltages	MCR22-6 MCR22-8	400 600	V
$I_T (RMS)$	RMS on-state current (full sine wave)		1.5	A
$I_{TSM}$	Non-repetitive peak on-state current (full cycle, $T_j$ initial=25°C)		15	A

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal resistance, Junction to Case		-	-	50	°C/W
$R_{\theta JA}$	Thermal resistance, Junction to Ambient		-	-	160	°C/W

### HAOPIN MICROELECTRONICS CO.,LTD.

Limiting values in accordance with the Maximum system(IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state Voltages	$R_{GK}=1K, T_J=-40$ to $+110^{\circ}C$ MCR22-6 Sine wave,50to60 Hz,gate open MCR22-8	-	400 600	V
$I_{T(RMS)}$	RMS on-state current	$180^{\circ}$ Conduction Angles, $T_c=80^{\circ}C$	-	1.5	A
$I_{TSM}$	Non-repetitive peak Current	1/2Cycle,sine wave,60 Hz	-	15	A
$I^2t$	Circuit fusing considerations	$t=8.3ms$	-	0.9	$A^2S$
$I_{DRM}$ $I_{RRM}$	Peak repetitive forward or reverse blocking current	$V_{AK}=\text{Rated } V_{DRM}$ or $V_{RRM}$ $T_C=25^{\circ}C$ $R_{GK}=1000\text{Ohms}$ $T_C=110^{\circ}C$	-	10 200	$\mu A$ $\mu A$
$I_{FGM}$	Forward Peak gate current	$T_A=25^{\circ}C$ ,Pulse Width $\leq 1.0 \mu s$	-	0.2	A
$V_{RGM}$	Reverse Peak gate voltage	$T_A=25^{\circ}C$ ,Pulse Width $\leq 1.0 \mu s$	-	5	V
$P_{GM}$	Peak gate power	$T_A=25^{\circ}C$ ,Pulse Width $\leq 1.0 \mu s$	-	0.5	W
$P_{G(AV)}$	Average gate power	$T_A=25^{\circ}C$ ,Pulse Width $\leq 1.0 \mu s$	-	0.1	W
$T_{stg}$	Storage temperature		-40	150	$^{\circ}C$
$T_j$	Operating junction Temperature Range		-	110	$^{\circ}C$

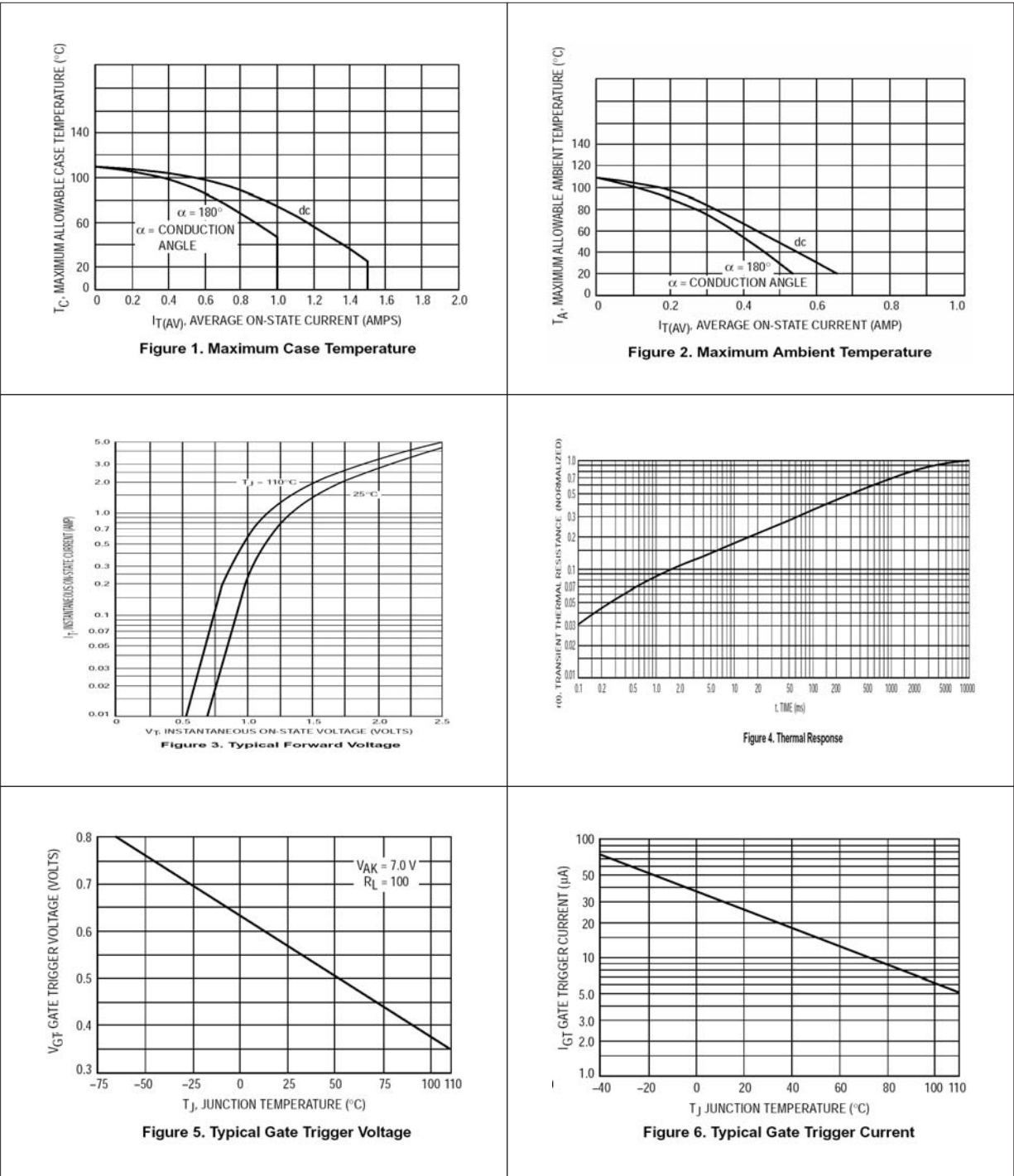
$T_J=25^{\circ}C$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
$I_{GT}$	Gate trigger current	$V_{AK}=6.0Vdc, RL=100 \text{ Ohms}$ $T_c=25^{\circ}C$ $T_c=-40^{\circ}C$	-	30 -	200 500	$\mu A$
$T_L$	Lead solder Temperature	Lead Length $\geq 1/16$ from case,10s Max	-	-	260	$^{\circ}C$
$I_H$	Holding current	$V_{AK}=12Vdc$ ,Initiating Current=200mA $T_C=25^{\circ}C$ $T_C=-40^{\circ}C$	-	2.0 -	5.0 10	mA mA
$V_{TM}$	On-state voltage	$I_{TM}=1.0A$ Peak	-	1.2	1.7	V
$V_{GT}$	Gate trigger voltage	$V_{AK}=7.0Vdc, RL=100 \text{ Ohms}$ $T_C=25^{\circ}C$ $T_C=-40^{\circ}C$	- -	- -	0.8 1.2	V V

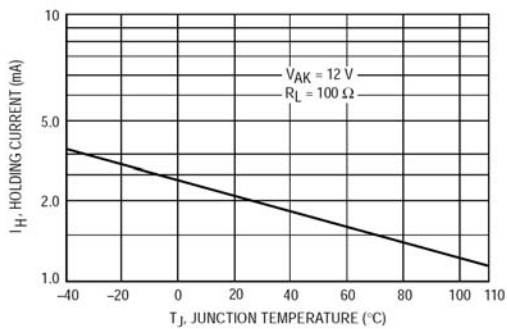
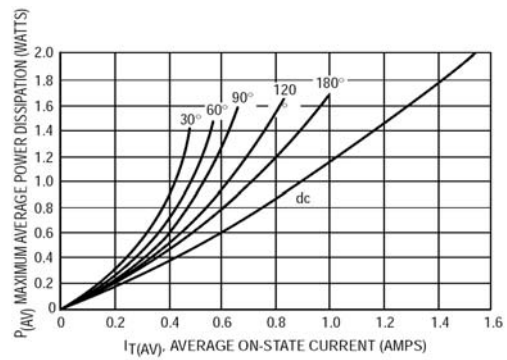
### Dynamic Characteristics

$D_v/dt$	Critical rate of rise of Off-state voltage	$T_c=110^{\circ}C$	-	25	-	V/ $\mu s$
$di/dt$	Critical Rate-of-Rise of Off State Current		-	-	-	A/ $\mu s$

#### Description



Description

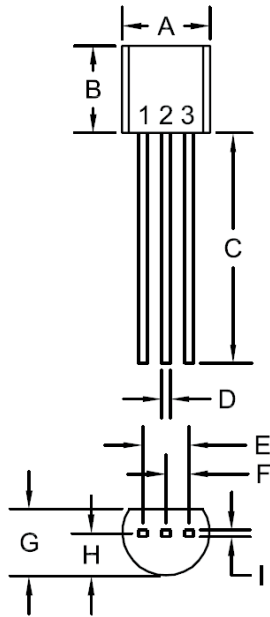
 <p><b>Figure 7. Typical Holding Current</b></p>	 <p><b>Figure 8. Power Dissipation</b></p>

MECHANICAL DATA

Dimensions in mm

Net Mass:0.2 g

TO-92



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R1